MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

2SA1201-x-MS

Product specification





TRANSISTOR (PNP)

FEATURE

- High voltage
- High transition frequency
- Complementary to 2SC2881-x-MS

Reference News



MARKING

2SA1201-O-MS	2SA1201-Y-MS
DO	DY

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
Vсво	Collector-Base Voltage	-120	V
VCEO	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-0.8	Α
Pc	Collector Power Dissipation	0.5	W
TJ	Junction Temperature	150	$^{\circ}$ C
T _{stg}	Storage Temperature	-55-150	$^{\circ}$
R өJA	Thermal Resistance from Junction to Ambient	250	$^{\circ}$ C



ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

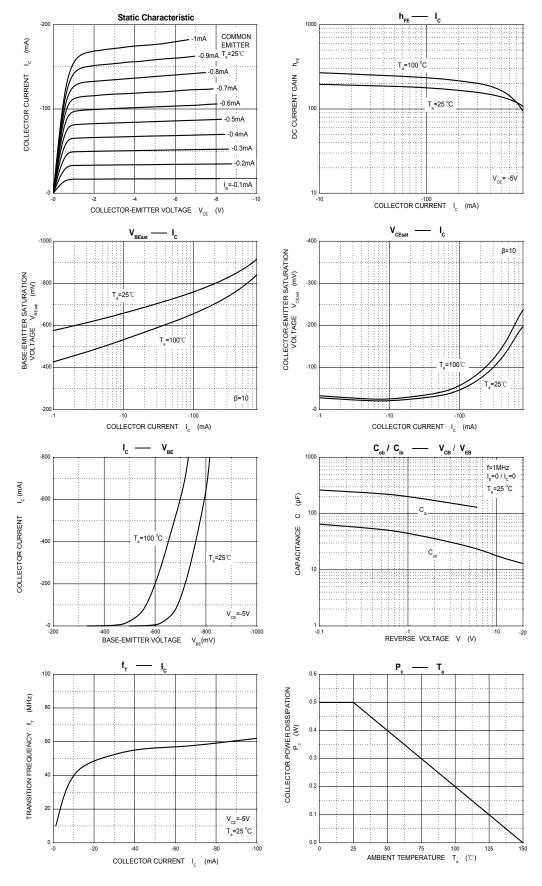
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA,I _E =0	-120			٧
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-120			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA,I _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-120V,I _E =0			-0.1	μA
Emitter cut-off current	ГЕВО	V _{EB} =-5V,I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-5V,I _C =-100mA	80		240	
Collector-emitter saturation voltage	V _{CE(sat)}	Ic=-500mA,I _B =-50mA			-1	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V,I _C =-500mA			-1	٧
Transition frequency	f⊤	V _{CE} =-5V,I _C =-100mA		120		MHz
Collector output capacitance	Cob	V _{CB} =-10V,I _E =0,f=1MHz			30	pF

CLASSIFICATION OF hFE

Rank	2SA1201-O-MS	2SA1201-Y-MS
Range	80-160	120-240

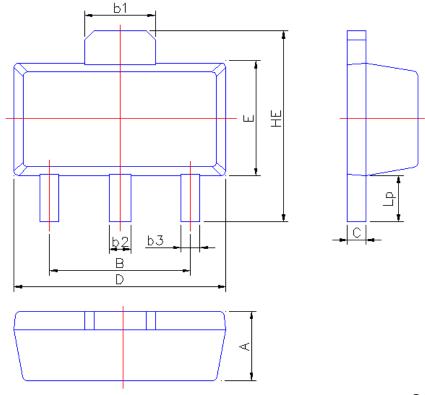


Typical Characteristics





PACKAGE MECHANICAL DATA



SOT-89

	Dimension in Millimeters		
Symbol	Min	Max	
А	1.40	1.60	
В	2.95	3.05	
b1	1.45	1.70	
b2	0.45	0.60	
b3	0.35	0.50	
С	0.35	0.50	
D	4.40	4.60	
E	2.35	2.55	
HE	3.90	4.40	
Lp	0.90	1.10	

REELSPECIFICATION

P/N	PKG	QTY
2SA1201-x-MS	SOT-89	1000



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